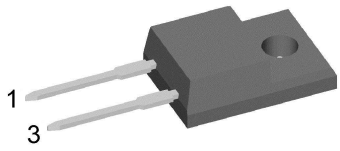
FRED

V_{RRM} = 600 V
I_{FAV} = 10 A
t_{rr} = 110 ns

Single Diode

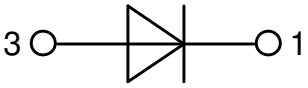
Part number

DFE10I600PM



Backside: Isolated

E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220FP

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Base plate: Plastic overmolded tab
- Reduced weight

Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.
Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.
Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend
- to perform joint risk and quality assessments;
- the conclusion of quality agreements;
- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions. Data according to IEC 60747and per semiconductor unless otherwise specified 20160920a

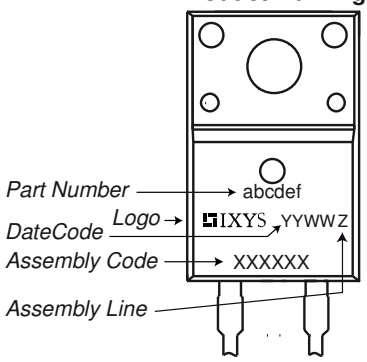
© 2016 IXYS all rights reserved

Fast Diode				Ratings			
Symbol	**Definition**	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			600	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			600	V
I_R	*reverse current, drain current*	V_R = 600 V	T_{VJ} = 25°C			20	µA
		V_R = 480 V	T_{VJ} = 125°C			1.5	mA
V_F	*forward voltage drop*	I_F = 10 A	T_{VJ} = 25°C			1.50	V
		I_F = 20 A				1.77	V
		I_F = 10 A	T_{VJ} = 150°C			1.38	V
		I_F = 20 A				1.70	V
I_{FAV}	*average forward current*	T_C = 100°C	T_{VJ} = 150°C			10	A
		rectangular d = 0.5					
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 150°C			0.98	V
r_F	*slope resistance* }					28.7	mΩ
R_{thJC}	*thermal resistance junction to case*					4.2	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.50		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			30	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine; V_R = 0 V	T_{VJ} = 45°C			100	A
C_J	*junction capacitance*	V_R = 400 V f = 1 MHz	T_{VJ} = 25°C		5		pF
I_{RM}	*max. reverse recovery current*		T_{VJ} = 25°C		4		A
		I_F = 10 A; V_R = 300 V	T_{VJ} = 125°C		2		A
t_{rr}	*reverse recovery time*	$-di_F/dt$ = 100 A/µs	T_{VJ} = 25°C		110		ns
			T_{VJ} = 125°C		25		ns

© 2016 IXYS all rights reserved

Package TO-220FP					Ratings			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per terminal					20	A
T_{VJ}	*virtual junction temperature*				-55		150	°C
T_{op}	*operation temperature*				-55		125	°C
T_{stg}	*storage temperature*				-55		150	°C
Weight						2		g
M_D	*mounting torque*				0.4		0.6	Nm
F_C	*mounting force with clip*				20		60	N
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	3.2	2.7			mm
$d_{Spb/Apb}$			*terminal to backside*	2.5	2.5			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA		2500			V
		t = 1 minute			2100			V

Product Marking



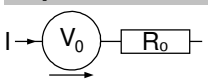
Part description

D = Diode
F = FRED
E = fast, low VF
10 = Current Rating [A]
I = Single Diode
600 = Reverse Voltage [V]
PM = TO-220ACFP (2)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DFE10I600PM	DFE10I600PM	Tube	50	503920

Similar Part	Package	Voltage class
DSEI8-06A	TO-220AC (2)	600
DSEI8-06AS	TO-263AB (D2Pak) (2)	600

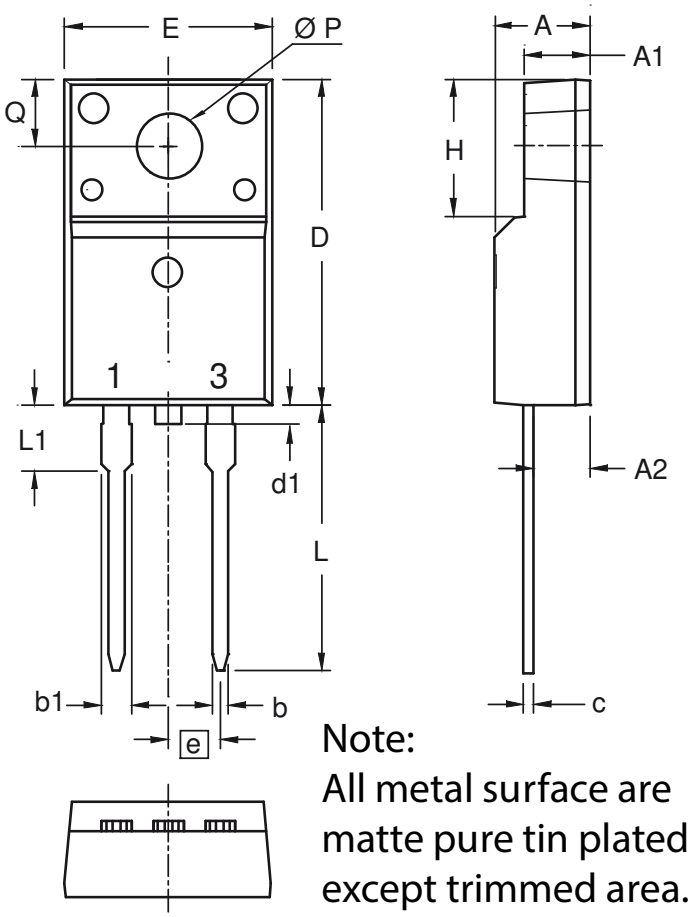
Equivalent Circuits for Simulation ** on die level* T_{VJ} = 150 °C



		Fast Diode	
$V_{0\,max}$	*threshold voltage*	0.98	V
$R_{0\,max}$	*slope resistance **	25.7	mΩ

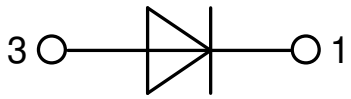
© 2016 IXYS all rights reserved

Outlines TO-220FP



Note:
All metal surface are matte pure tin plated except trimmed area.

Dim.	Millimeters		Inches	
	min	max	min	max
A	4.50	4.90	0.177	0.193
A1	2.34	2.74	0.092	0.108
A2	2.56	2.96	0.101	0.117
b	0.70	0.90	0.028	0.035
b1	1.27	1.47	0.050	0.058
c	0.45	0.60	0.018	0.024
D	15.67	16.07	0.617	0.633
d1	0	1.10	0	0.043
E	9.96	10.36	0.392	0.408
e	2.54 BSC		0.100 BSC	
H	6.48	6.88	0.255	0.271
L	12.68	13.28	0.499	0.523
L1	3.03	3.43	0.119	0.135
Ø P	3.08	3.28	0.121	0.129
Q	3.20	3.40	0.126	0.134



© 2016 IXYS all rights reserved

Fast Diode

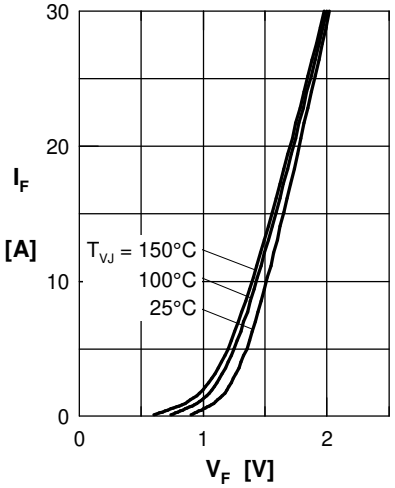


Fig. 1 Forward current I_F versus V_F

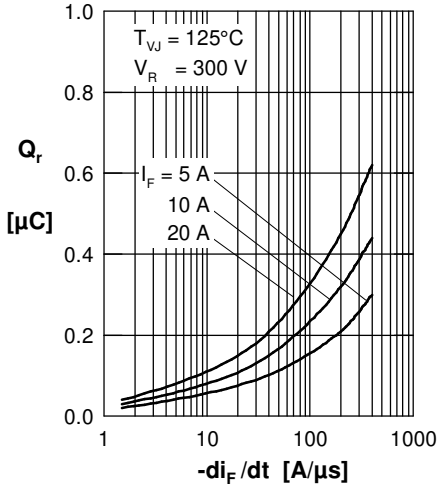


Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

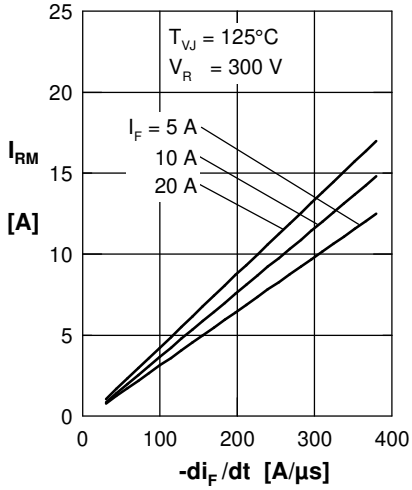


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

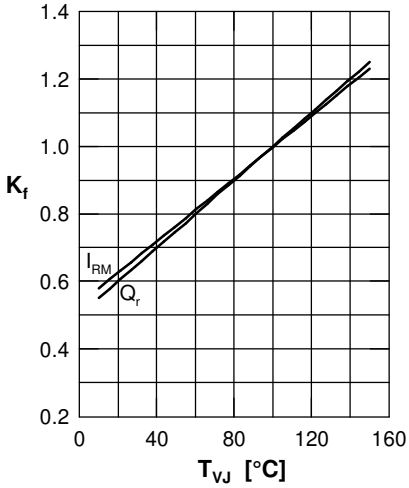


Fig. 4 Dyn. parameters Q_r, I_{RM} versus T_{VJ}

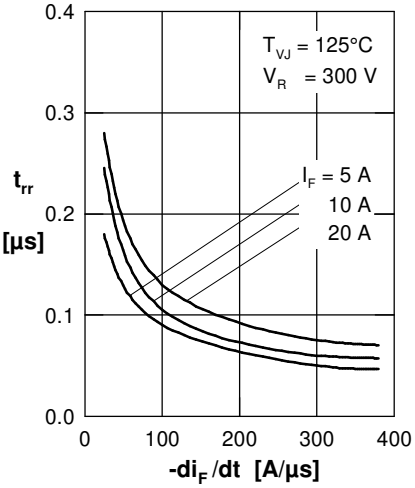


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

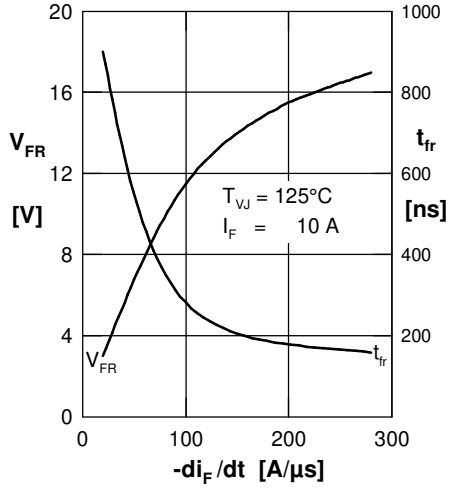


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

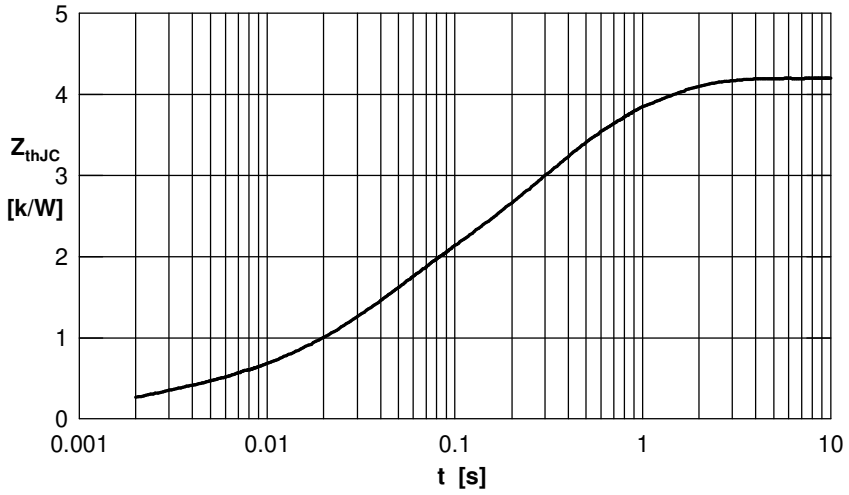


Fig. 7 Transient thermal impedance junction to case

© 2016 IXYS all rights reserved